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### FDA20N50F N-Channel UniFET<sup>TM</sup> FRFET<sup>®</sup> MOSFET 500 V, 22 A, 260 m $\Omega$

#### Features

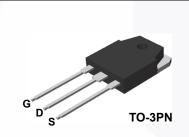
- R<sub>DS(on)</sub> = 220 mΩ (Typ.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 11 A
- Low Gate Charge (Typ. 50 nC)
- Low C<sub>rss</sub> (Typ. 27 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant

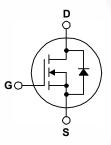
#### Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

#### Description

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET<sup>®</sup> MOSFET has been enhanced by lifetime control. Its trr is less than 100nsec and the reverse dv/dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp balasts.





#### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

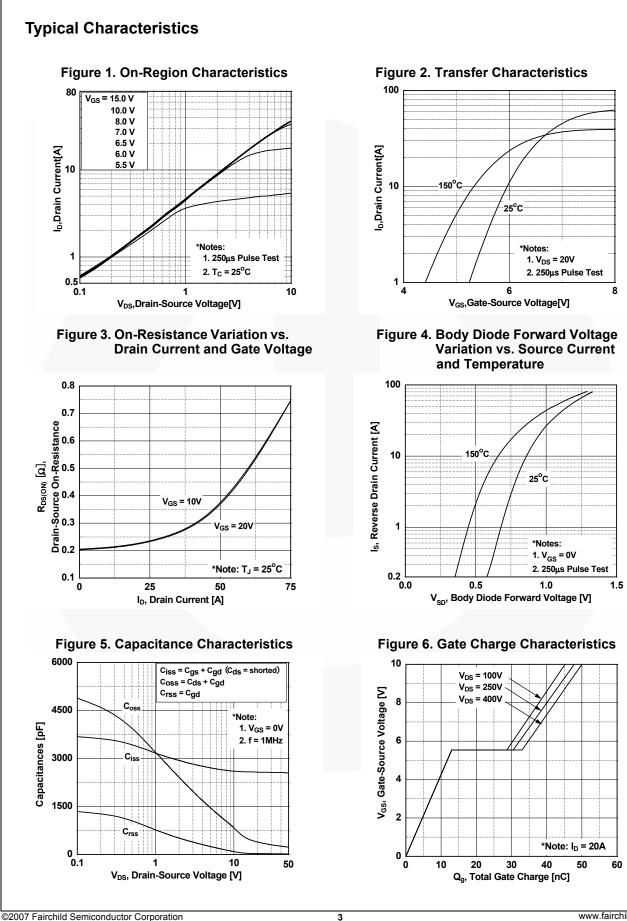
Symbol		FDA20N50F	Unit		
V <sub>DSS</sub>	Drain to Source Voltage	500	V		
V <sub>GSS</sub>	Gate to Source Voltage			±30	V
ID	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)	22	Α	
	Diamourient	- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)	13	— A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	88	Α
E <sub>AS</sub>	Single Pulsed Avalanche Er	(Note 2)	ote 2) 1110		
I <sub>AR</sub>	Avalanche Current	(Note 1)	22	A	
E <sub>AR</sub>	Repetitive Avalanche Energ	(Note 1)	(Note 1) 39		
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	20	V/ns	
P <sub>D</sub>	Devuer Dissinction	(T <sub>C</sub> = 25°C)		388	W
	Power Dissipation	- Derate above 25°C	3.1	W/ºC	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum Lead Temperature 1/8" from Case for 5 Second	300	°C		

#### Thermal Characteristics

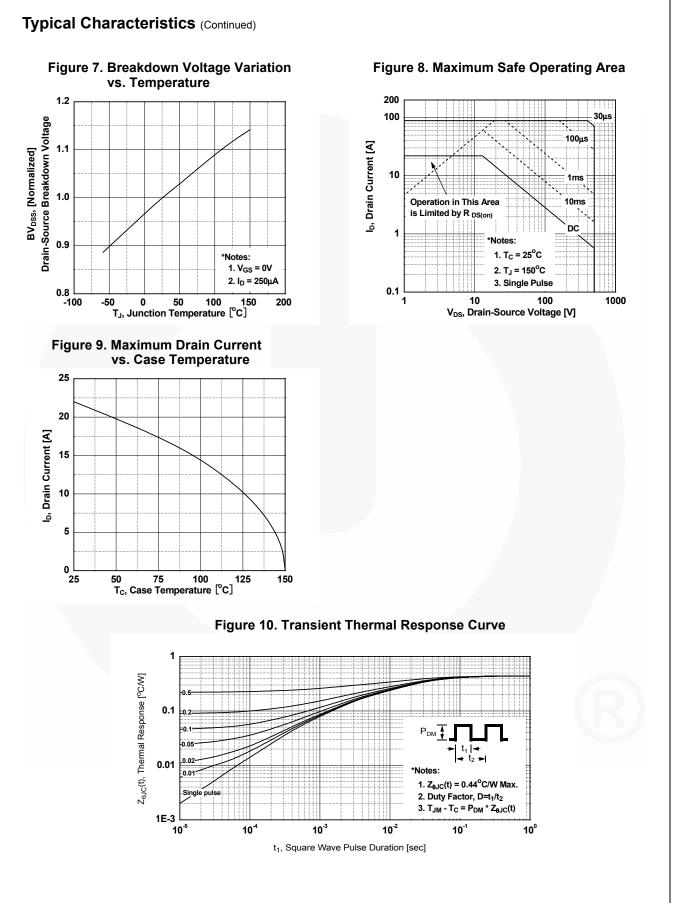
Symbol	Parameter	FDA20N50F	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.44	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/W	

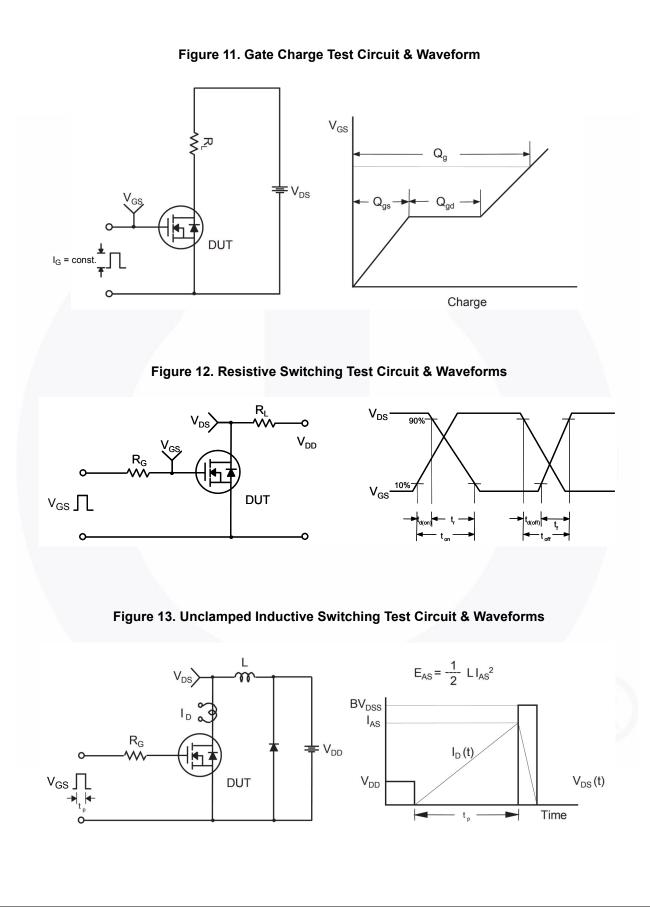
June 2014

	Device Marking Device Page		Pack	age	Reel Size	Таре	e Width		Quantit	у
FDA20N50F FDA20N50F TO-			BPN	Tube		N/A		30 units		
Electrica	l Char	acteristics T <sub>c</sub> =	25 <sup>0</sup> C unles	ss otherwise	noted.					
Symbol		Parameter			Test Conditions			Тур.	Max.	Unit
Off Charac	teristic	8								
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage		I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25°C			500	-	_	V	
ΔBV <sub>DSS</sub>		reakdown Voltage Temperature				500				
$/ \Delta T_J$		Coefficient		$I_{\rm D} = 250$	μA, Referenced	to 25°C	-	0.6	-	V/ºC
	Zero Gate Voltage Drain Current		nt		00V, V <sub>GS</sub> = 0V		-	-	10	μA
DSS	2010 00	Zero Gate Voltage Drain Current		-	00V, T <sub>C</sub> = 125ºC		-	-	100	μΑ
GSS	Gate to Body Leakage Current			V <sub>GS</sub> = ±	30V, V <sub>DS</sub> = 0V		-	-	±100	nA
On Charac	teristics	6								
V <sub>GS(th)</sub>	Gate Th	reshold Voltage	-	$V_{CS} = V$	<sub>DS</sub> , I <sub>D</sub> = 250μA		3.0	-	5.0	V
R <sub>DS(on)</sub>		Static Drain to Source On Resistance		$V_{GS} = 10V, I_D = 11A$			-	0.22	0.26	Ω
9FS	Forward Transconductance			$V_{DS} = 40V, I_D = 11A$			-	24	-	S
	`h a ra ata	riation		20						
Dynamic C	1		_				-	2550	3390	۶E
C <sub>iss</sub>		apacitance Capacitance		— V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V — f = 1MHz		-	-	350	465	pF pF
C <sub>oss</sub>		Transfer Capacitance				-		27	403	pF
C <sub>rss</sub>		te Charge at 10V		V <sub>DS</sub> = 400V, I <sub>D</sub> = 20A V <sub>GS</sub> = 10V			-	50	65	nC
Q <sub>g(tot)</sub> Q <sub>gs</sub>		Source Gate Charge				+	-	14	-	nC
Q <sub>gd</sub>		Drain "Miller" Charge					-	20	-	nC
agd		Drain winer onarge				(Note 4)	_	20		
Switching	Charact	teristics								
t <sub>d(on)</sub>	Turn-On	Delay Time					-	45	100	ns
t <sub>r</sub>	Turn-On	Rise Time		$V_{DD} = 250V, I_D = 20A$		-	120	250	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time		$R_{G} = 25\Omega$		-	100	210	ns		
t <sub>f</sub>	Turn-Off	Fall Time			(Note 4)		-	60	130	ns
Drain-Sou	rce Dioc	le Characteristics								
I <sub>S</sub>	T	m Continuous Drain to		de Forward	Current		-	_	22	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Fo				-	-	88	Α		
V <sub>SD</sub>	Drain to	Drain to Source Diode Forward Voltage		V <sub>GS</sub> = 0V, I <sub>SD</sub> = 22A			-	-	1.5	V
		Recovery Time			V, I <sub>SD</sub> = 20A		-	154	-	ns
t <sub>rr</sub>	Reverse	Recovery Charge			100A/µs		-	0.5	-	μC



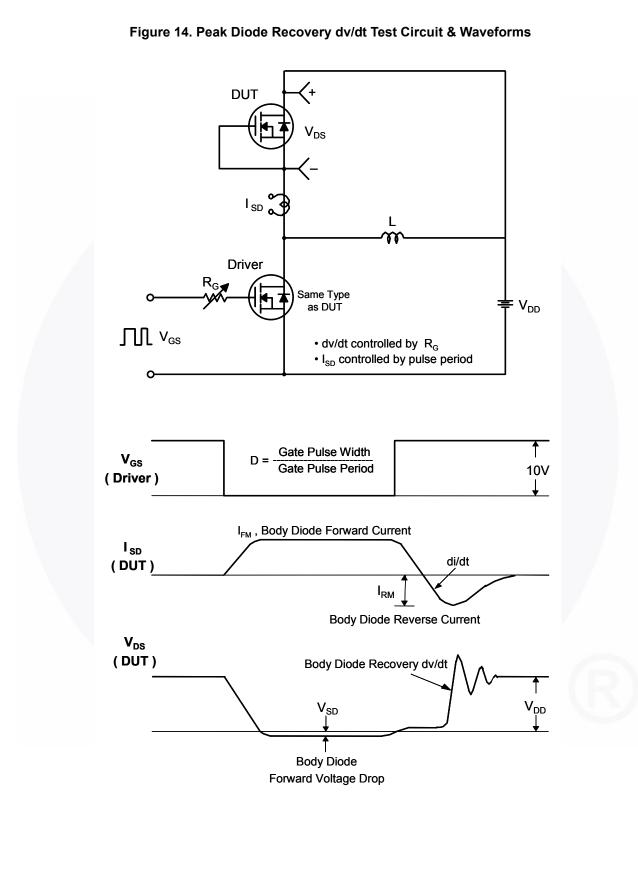
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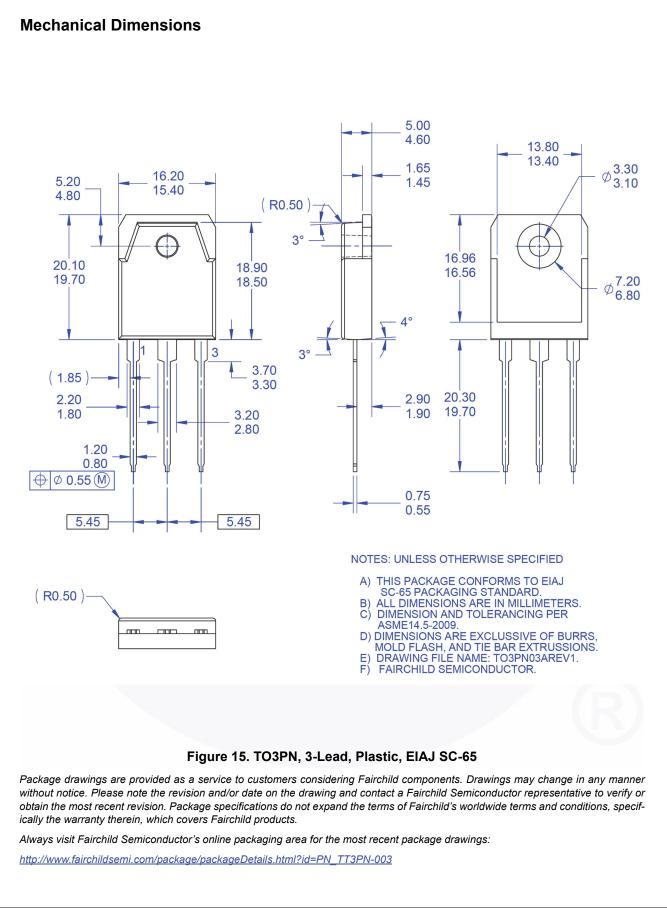




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FDA20N50F ---

N-Channel UniFET<sup>TM</sup> FRFET<sup>®</sup> MOSFET



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